

# Phase Control Thyristors (Hockey PUK Version), 500 A



A-PUK (TO-200AB)

| PRIMARY CHARACTERISTICS            |                   |  |  |  |  |
|------------------------------------|-------------------|--|--|--|--|
| I <sub>T(AV)</sub>                 | 500 A             |  |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 400 V, 600 V      |  |  |  |  |
| V <sub>TM</sub>                    | 1.35 V            |  |  |  |  |
| I <sub>GT</sub>                    | 90 mA             |  |  |  |  |
| T <sub>J</sub>                     | -40 °C to +150 °C |  |  |  |  |
| Package                            | A-PUK (TO-200AB)  |  |  |  |  |
| Circuit configuration              | Single SCR        |  |  |  |  |

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)



- Extended temperature range
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

| MAJOR RATINGS AND CHARACTERISTICS  |                 |            |                   |  |  |  |
|------------------------------------|-----------------|------------|-------------------|--|--|--|
| PARAMETER                          | TEST CONDITIONS | VALUES     | UNITS             |  |  |  |
| ı                                  |                 | 500        | Α                 |  |  |  |
| I <sub>T(AV)</sub>                 | T <sub>hs</sub> | 80         | °C                |  |  |  |
| I <sub>T(RMS)</sub>                |                 | 1130       | А                 |  |  |  |
|                                    | T <sub>hs</sub> | 25         | °C                |  |  |  |
| I <sub>TSM</sub>                   | 50 Hz           | 7200       | A                 |  |  |  |
|                                    | 60 Hz           | 7500       | A                 |  |  |  |
| l <sup>2</sup> t                   | 50 Hz           | 260        | kA <sup>2</sup> s |  |  |  |
|                                    | 60 Hz           | 230        |                   |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> |                 | 400 to 600 | V                 |  |  |  |
| t <sub>q</sub>                     | Typical         | 100        | μs                |  |  |  |
| T <sub>J</sub>                     |                 | -40 to 150 | °C                |  |  |  |

#### **ELECTRICAL SPECIFICATIONS**

| VOLTAGE RATINGS |                 |   |  |  |  |  |  |
|-----------------|-----------------|---|--|--|--|--|--|
| TYPE NUMBER     | VOLTAGE<br>CODE | V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM<br>REPETITIVE PEAK AND<br>OFF-STATE VOLTAGE<br>V | V <sub>RSM</sub> , MAXIMUM<br>NON-REPETITIVE PEAK VOLTAGE<br>V | $\begin{array}{l} I_{DRM}/I_{RRM} \ MAXIMUM \\ AT \ T_J = T_J \ MAXIMUM \\ mA \end{array}$ |  |  |  |
| VS-ST280CHC     | 04              | 400   | 500  | 75   |  |  |  |
| V3-31200CHC     | 06              | 600   | 700  | 75   |  |  |  |



| ABSOLUTE MAXIMUM RATINGS                      | 3                    |  |  |                             |            |                        |
|---|----------------------|--|--|-----------------------------|------------|------------------------|
| PARAMETER                                     | SYMBOL               |  | TEST CONDITIONS  |                             |            | UNITS                  |
| Maximum average on-state current              | <b>I</b>             | 180° condu   | 180° conduction, half sine wave  |                             |            | Α                      |
| at heatsink temperature                       | I <sub>T(AV)</sub>   | double side  | (single side) co   | oled                        | 80 (110)   | °C                     |
| Maximum RMS on-state current                  | I <sub>T(RMS)</sub>  | DC at 25 °C  | heatsink tempe   | erature double side cooled  | 1130       |                        |
|   |                      | t = 10 ms  | No voltage   |                             | 7200       |                        |
| Maximum peak, one-cycle                       |                      | t = 8.3 ms   | reapplied  |                             | 7500       | A<br>kA <sup>2</sup> s |
| non-repetitive surge current                  | I <sub>TSM</sub>     | t = 10 ms  | 100 % V <sub>RRM</sub>   |                             | 6000       |                        |
|   |                      | t = 8.3 ms   | reapplied  | Sinusoidal half wave.       | 6300       |                        |
| Maximum I <sup>2</sup> t for fusing           |                      | t = 10 ms  | No voltage reapplied   | initial $T_J = T_J$ maximum | 260        |                        |
|   | l <sup>2</sup> t     | t = 8.3 ms   |  |                             | 235        |                        |
|   |                      | t = 10 ms  | 100 % V <sub>RRM</sub>   |                             | 180        |                        |
|   | t = 8.3 ms reapplied |  |  | 165                         |            |                        |
| Maximum I <sup>2</sup> √t for fusing          | I <sup>2</sup> √t    | t = 0.1 to 10  | t = 0.1 to 10 ms, no voltage reapplied   |                             |            | kA²√s                  |
| Low level value of threshold voltage          | V <sub>T(TO)1</sub>  | (16.7 % x π  | (16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum |                             |            | V                      |
| High level value of threshold voltage         | V <sub>T(TO)2</sub>  | $(I > \pi \times I_{T(AV)})$   | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$                        |                             |            | \ \ \                  |
| Low level value of on-state slope resistance  | r <sub>t1</sub>      | (16.7 % x π  | (16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum |                             |            | mΩ                     |
| High level value of on-state slope resistance | r <sub>t2</sub>      | $(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum                                   |  |                             | 0.47       | 1115.2                 |
| Maximum on-state voltage                      | $V_{TM}$             | $I_{pk} = 1000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$ |  |                             | 1.35       | V                      |
| Maximum holding current                       | I <sub>H</sub>       | T 05 °C  | anada ayanlı 1   | O V registive lead          | 600        | A                      |
| Maximum (typical) latching current            | ΙL                   | 1 J = 25 °C,   | anoue supply 1   | 2 V resistive load          | 1000 (300) | mA                     |

| SWITCHING  |                |   |        |       |
|--|----------------|---|--------|-------|
| PARAMETER  | SYMBOL         | TEST CONDITIONS   | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned-on current | dl/dt          | Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$                         | 1000   | A/µs  |
| Typical delay time                                       | t <sub>d</sub> | Gate current 1 A, $dl_g/dt = 1 A/\mu s$<br>$V_d$ 0.67 % $V_{DRM}$ , $T_J = 25 ^{\circ}C$  | 1.0    | 9     |
| Typical turn-off time                                    | t <sub>q</sub> | $I_{TM}$ = 300 A, $T_J$ = $T_J$ maximum, dl/dt = 20 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs | 100    | μs    |

| BLOCKING   |  |   |        |           |  |  |
|--|--|---|--------|-----------|--|--|
| PARAMETER  | SYMBOL                                 | TEST CONDITIONS   | VALUES | UNIT<br>S |  |  |
| Maximum critical rate of rise of off-state voltage | dV/dt                                  | T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub> | 500    | V/µs      |  |  |
| Maximum peak reverse and off-state leakage current | I <sub>RRM</sub> ,<br>I <sub>DRM</sub> | $T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied                          | 75     | mA        |  |  |



| TRIGGERING                          |                         |                                     |  |      |        |       |  |
|-------------------------------------|-------------------------|-------------------------------------|--|------|--------|-------|--|
| PARAMETER                           | SYMBOL                  | TE                                  | TEST COMPLIANCE  |      | VALUES |       |  |
| PANAMETEN                           | STINIBUL                | ''                                  | ST CONDITIONS  | TYP. | MAX.   | UNITS |  |
| Maximum peak gate power             | $P_{GM}$                | $T_J = T_J$ maximum,                | $t_p \leq 5 \ ms$  | 10   | 0.0    | W     |  |
| Maximum average gate power          | P <sub>G(AV)</sub>      | $T_J = T_J$ maximum,                | f = 50 Hz, d% = 50   | 2    | .0     | VV    |  |
| Maximum peak positive gate current  | I <sub>GM</sub>         | $T_J = T_J$ maximum,                | $t_p \leq 5 \ ms$  | 3    | .0     | Α     |  |
| Maximum peak positive gate voltage  | + V <sub>GM</sub>       | 20                                  |  | 0    | V      |       |  |
| Maximum peak negative gate voltage  | - V <sub>GM</sub>       | $T_J = T_J$ maximum, $t_p \le 5$ ms |  |      | 5.0    |       |  |
|                                     | I <sub>GT</sub>         | T <sub>J</sub> = - 40 °C            |  | 180  | -      |       |  |
| DC gate current required to trigger |                         | T <sub>J</sub> = 25 °C              |  | 90   | 150    | mA    |  |
|                                     |                         | T <sub>J</sub> = 150 °C             | T <sub>J</sub> = 150 °C Maximum required gate trigger/ current/voltage are the lowest      |      | -      |       |  |
|                                     |                         | T <sub>J</sub> = - 40 °C            | value which will trigger all units 12 V anode to cathode applied                           | 2.9  | -      |       |  |
| DC gate voltage required to trigger | $V_{GT}$                | T <sub>J</sub> = 25 °C              | 12 v anode to cathode applied  | 1.8  | 3.0    | V     |  |
|                                     | T <sub>J</sub> = 150 °C |                                     |  | 1.0  | -      |       |  |
| DC gate current not to trigger      | I <sub>GD</sub>         | T T                                 | Maximum gate current/voltage not to trigger is the maximum                                 | 1    | 0      | mA    |  |
| DC gate voltage not to trigger      | V <sub>GD</sub>         | $T_J = T_J \text{ maximum}$         | value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied | 0.30 |        | V     |  |

| THERMAL AND MECHANICAL SPECIFICATIONS                    |                                   |   |               |           |  |  |
|--|-----------------------------------|---|---------------|-----------|--|--|
| PARAMETER  | SYMBOL                            | TEST CONDITIONS                               | VALUES        | UNITS     |  |  |
| Maximum operating junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |   | - 40 to 150   | °C        |  |  |
| Maximum thermal resistance,                              | В                                 | DC operation single side cooled               | 0.17          |           |  |  |
| junction to heatsink                                     | R <sub>thJ-hs</sub>               | DC operation double side cooled               | 0.08          | K/W       |  |  |
| Maximum thermal resistance,                              | Б                                 | DC operation single side cooled               | 0.033         | T N VV    |  |  |
| case to heatsink   | R <sub>thC-hs</sub>               | DC operation double side cooled               | 0.017         |           |  |  |
| Mounting force, ± 10 %                                   |                                   |   | 4900<br>(500) | N<br>(kg) |  |  |
| Approximate weight                                       |                                   |   | 50            | g         |  |  |
| Case style   |                                   | See dimensions - link at the end of datasheet | A-PUK (TO-2   | 200AB)    |  |  |

| △R <sub>thJ-hs</sub> CONDUCTION |             |             |             |             |                     |       |
|---------------------------------|-------------|-------------|-------------|-------------|---------------------|-------|
| CONDUCTION ANGLE                | SINUSOIDAL  | CONDUCTION  | RECTANGULAR | CONDUCTION  | TEST CONDITIONS     | UNITS |
| CONDUCTION ANGLE                | SINGLE SIDE | DOUBLE SIDE | SINGLE SIDE | DOUBLE SIDE | TEST CONDITIONS     | UNITS |
| 180°                            | 0.016       | 0.017       | 0.011       | 0.011       | $T_J = T_J$ maximum |       |
| 120°                            | 0.019       | 0.019       | 0.019       | 0.019       |                     |       |
| 90°                             | 0.024       | 0.024       | 0.026       | 0.026       |                     | K/W   |
| 60°                             | 0.035       | 0.035       | 0.036       | 0.037       |                     |       |
| 30°                             | 0.060       | 0.060       | 0.060       | 0.061       |                     |       |

#### Note

<sup>•</sup> The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC



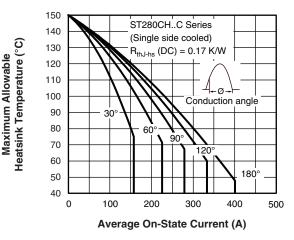
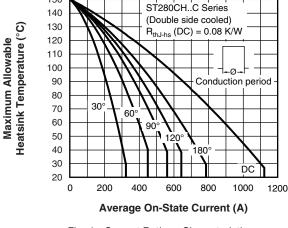


Fig. 1 - Current Ratings Characteristics



150

Fig. 4 - Current Ratings Characteristics

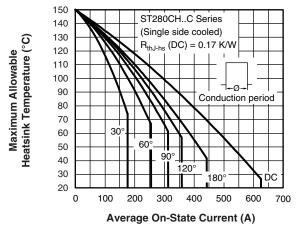


Fig. 2 - Current Ratings Characteristics

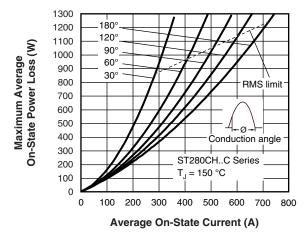


Fig. 5 - On-State Power Loss Characteristics

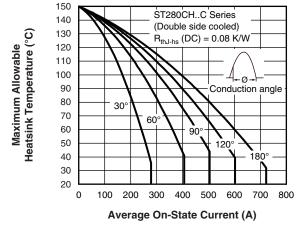


Fig. 3 - Current Ratings Characteristics

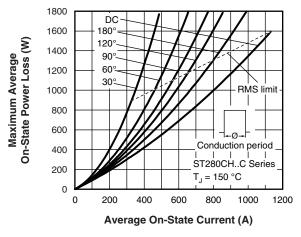


Fig. 6 - On-State Power Loss Characteristics



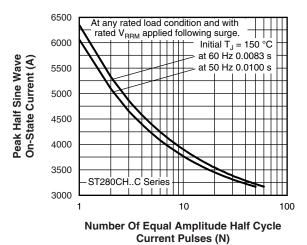


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

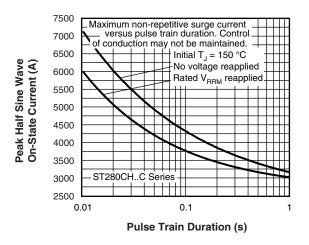


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

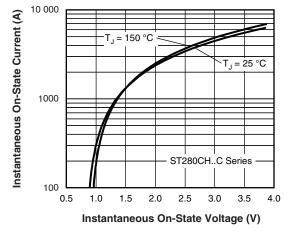


Fig. 9 - On-State Voltage Drop Characteristics

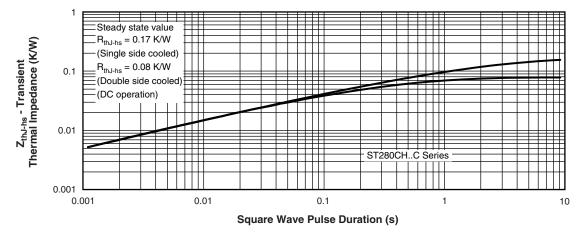


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

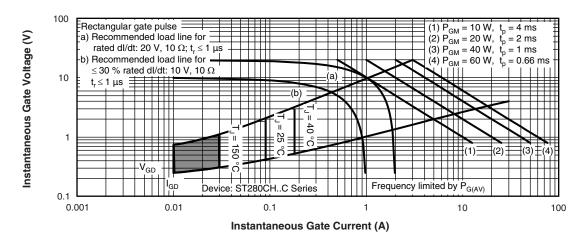
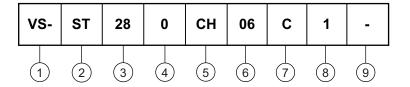


Fig. 11 - Gate Characteristics

# ORDERING INFORMATION TABLE

#### Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - CH = ceramic PUK, high temperature

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - C = PUK case A-PUK (TO-200AB)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

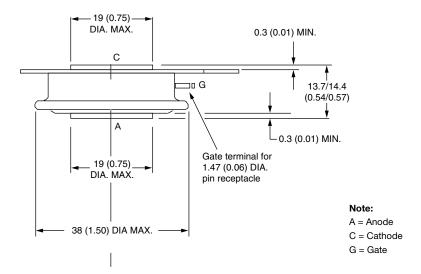
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |
|----------------------------|--------------------------|--|--|--|
| Dimensions                 | www.vishay.com/doc?95074 |  |  |  |

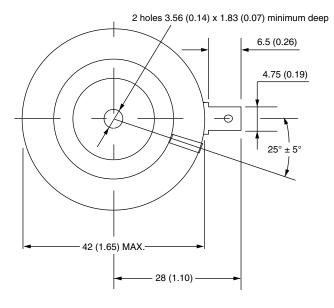


# **A-PUK (TO-200AB)**

#### **DIMENSIONS** in millimeters (inches)

Anode to gate Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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